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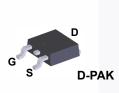
## FCD7N60 N-Channel SuperFET<sup>®</sup> MOSFET 600 V, 7 A, 600 mΩ

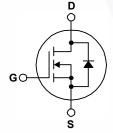
## Features

- 650 V @ T<sub>.1</sub> = 150°C
- Typ. R<sub>DS(on)</sub> = 530 mΩ
- Ultra Low Gate Charge (Typ. Q<sub>q</sub> = 23 nC)
- Low Effective Output Capacitance (Typ. C<sub>oss(eff.)</sub> = 60 pF)
- 100% Avalanche Tested
- RoHS Compliant

## Application

- LCD / LED TV and Monitor
- Lighting
- Solar Inverter
- AC-DC Power Supply





 $SuperFET^{\textcircled{M}}MOSFET$  is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is

utilizing charge balance technology for outstanding low on-

resistance and lower gate charge performance. This technology

is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Con-

sequently, SuperFET MOSFET is very suitable for the switching

power applications such as PFC, server/telecom power, FPD

TV power, ATX power and industrial power applications.

Description

### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter			FCD7N60TM / FCD7N60TM_WS	Unit V
V <sub>DSS</sub> Drain to Source Voltage			600		
ID	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		7	
	Drain Current	- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)		4.4	- A
I <sub>DM</sub>	Drain Current	- Pulsed	- Pulsed (Note 1)		Α
V <sub>GSS</sub>	Gate to Source Voltage			±30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy		(Note 2)	230	mJ
I <sub>AR</sub>	Avalanche Current		(Note 1)	7	Α
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	8.3	mJ
dv/dt	Peak Diode Recovery dv/dt (Note:		(Note 3)	20	V/ns
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C)		83	W
		- Derate Above 25°C		0.67	W/ºC
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		econds	300	°C

## **Thermal Characteristics**

Symbol	Parameter	FCD7N60TM / FCD7N60TM_WS	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.5	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient, Max.	83	0.00

December 2013

FCD7N60
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I SuperFET®
MOSFET

FCD7N60TM FCD7N60 D-		Top Mark	Packag	ge	Packing Method	Reel Size	Тар	e Width	Qua	ntity	
		FCD7N60	D-PAK	<	Tape and Reel	330 mm	1	6 mm	2500	2500 units	
		D-PAł	AK Tape and Reel 330 mm		330 mm	16 mm		2500 units			
Floctrica	l Chara	cteristics T <sub>c</sub> = 25		othe	nviso notod				-		
Symbol		Parameter	C uniess		Test Conditio	ons	Min.	Тур.	Max.	Unit	
Off Charac	teristics							.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,			
				Vc	<sub>is</sub> = 0 V, I <sub>D</sub> = 250 μA	T <sub>C</sub> = 25 <sup>o</sup> C	600	-	-	V	
BV <sub>DSS</sub> Drain to Source Breakdown Voltage		age	$V_{GS} = 0 V, I_D = 250 \mu A, T_C = 150^{\circ}C$		-	650	-	V			
ΔΒV <sub>DSS</sub> / ΔΤ.I	Breakdown Voltage Temperature			$I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		-	0.6	-	V/°C		
BV <sub>DS</sub>	Drain to S Voltage	Source Avalanche Breal	kdown	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 7.0 A		-	700	-	V		
				VD	$v_{\rm S}$ = 600 V, V <sub>GS</sub> = 0 V	'	-	-	1	μA	
IDSS	Zero Gale	ero Gate Voltage Drain Current		V <sub>DS</sub> = 480 V, T <sub>C</sub> = 125 <sup>o</sup> C		-	-	10	μΑ		
I <sub>GSS</sub>	Gate to B	ody Leakage Current		$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V		-	-	±100	nA		
On Charac	teristics										
V <sub>GS(th)</sub>	Gate Threshold Voltage			$V_{GS} = V_{DS}, I_{D} = 250 \ \mu A$		3.0	-	5.0	V		
R <sub>DS(on)</sub>	Static Drain to Source On Resistance			$_{SS} = 10 \text{ V}, \text{ I}_{D} = 3.5 \text{ A}$		-	0.53	0.6	Ω		
9 <sub>FS</sub>	Forward 7	Forward Transconductance		V <sub>DS</sub> = 40 V, I <sub>D</sub> = 3.5 A		-	6	-	S		
Dynamic C	haracter	istics									
C <sub>iss</sub>	Input Cap	acitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		-	710	920	pF		
C <sub>oss</sub>	Output Ca	apacitance				-	380	500	pF		
C <sub>rss</sub>	Reverse 7	Fransfer Capacitance				-	34	-	pF		
C <sub>oss</sub>	Output Capacitance		$V_{DS}$ = 480 V, $V_{GS}$ = 0 V, f = 1 MHz		-	22	29	pF			
C <sub>oss(eff.)</sub>	Effective Output Capacitance			$V_{DS}$ = 0 V to 400 V, $V_{GS}$ = 0 V		-	60	-	pF		
Switching	Characte	eristics									
t <sub>d(on)</sub>	Turn-On E	Delay Time						35	80	ns	
t <sub>r</sub>	Turn-On Rise Time Turn-Off Delay Time		V <sub>DD</sub> = 300 V, I <sub>D</sub> = 7.0 A,		-	55	120	ns			
t <sub>d(off)</sub>			Ve	$V_{GS}$ = 10 V , $R_{G}$ = 25 $\Omega$		-	75	160	ns		
t <sub>f</sub>	Turn-Off F	all Time		(Note 4)		7-	32	75	ns		
Q <sub>g(tot)</sub>	Total Gate	Charge at 10V		V	<sub>os</sub> = 480 V, I <sub>D</sub> = 7.0 A	. ,	-	23	30	nC	
Q <sub>gs</sub>		ource Gate Charge	-		$V_{\rm GS} = 480$ V, $T_{\rm D} = 7.0$ A, $V_{\rm GS} = 10$ V		-	4.2	5.5	nC	
Q <sub>gd</sub>	Gate to D	ain "Miller" Charge		(Note 4)		-	11.5	-	nC		
	ce Diode	Characteristics									
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current				-	-	7	A			
	Maximum Pulsed Drain to Source Diode Fo				-		21	A			
I <sub>SM</sub> V <sub>SD</sub>		ource Diode Forward V				-	· .	1.4	V		
		Recovery Time	onugo	$V_{GS} = 0 V, I_{SD} = 7.0 A$ $V_{GS} = 0 V, I_{SD} = 7.0 A,$ $dI_F/dt = 100 A/\mu s$				360	-		
t <sub>rr</sub>	Reverse F	kecoverv Lime							ns		

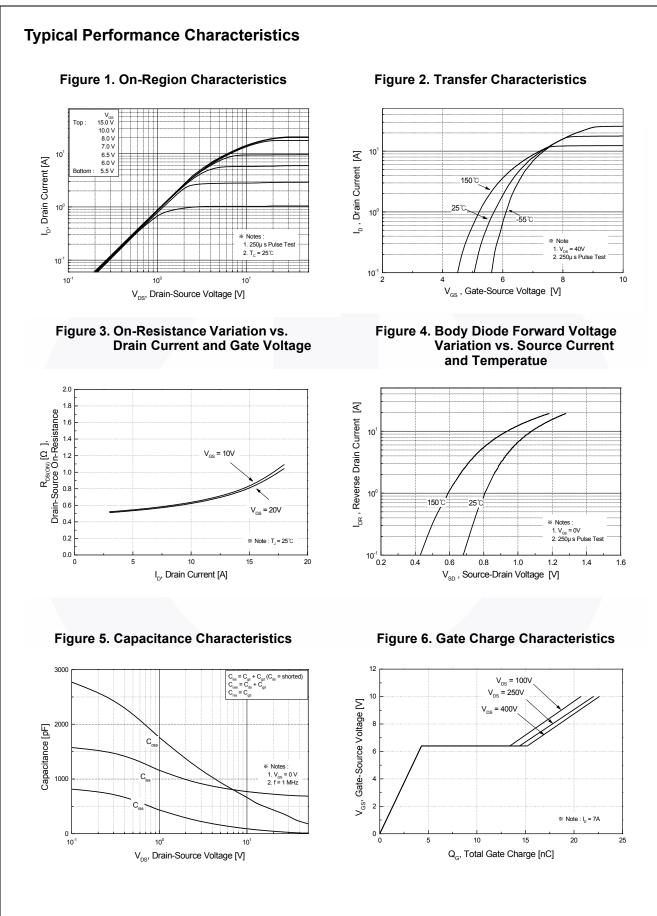
Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.

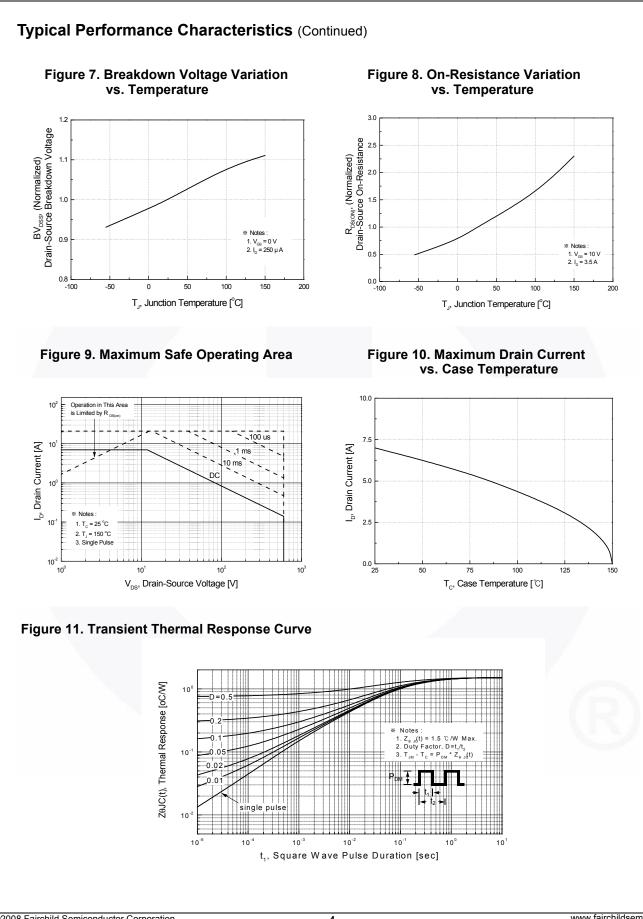
2.  $I_{AS}$  = 3.5 A,  $V_{DD}$  = 50 V,  $R_{G}$  = 25  $\Omega,$  starting  $T_{J}$  = 25°C.

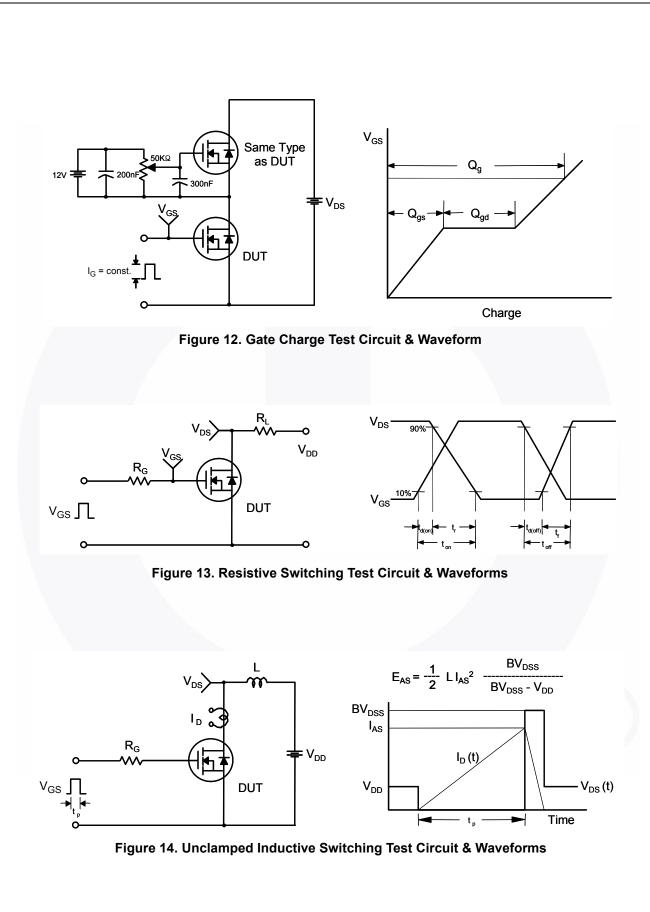
3.  $I_{SD} \le$  7 A, di/dt  $\le$  200 A/µs,  $V_{DD} \le$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C.

4. Essentially independent of operating temperature typical characteristics.

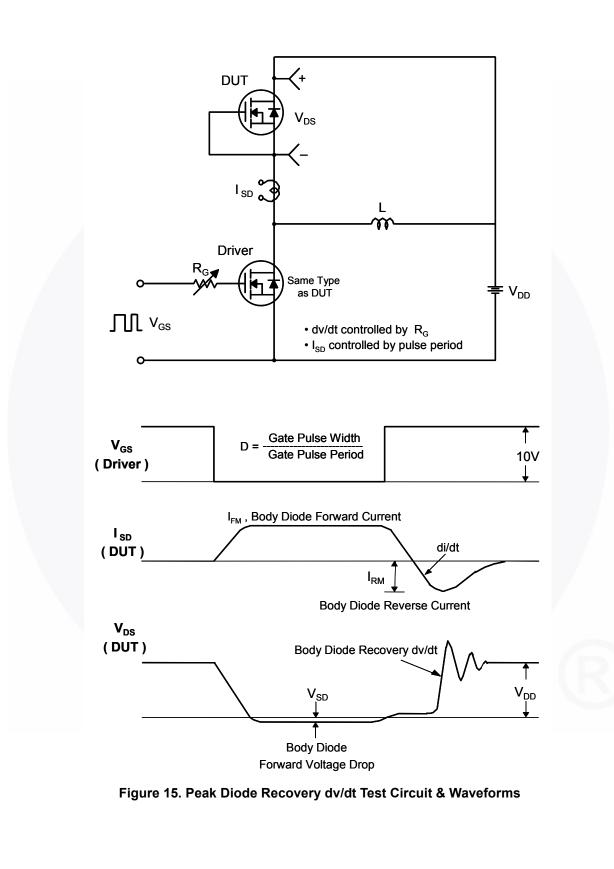


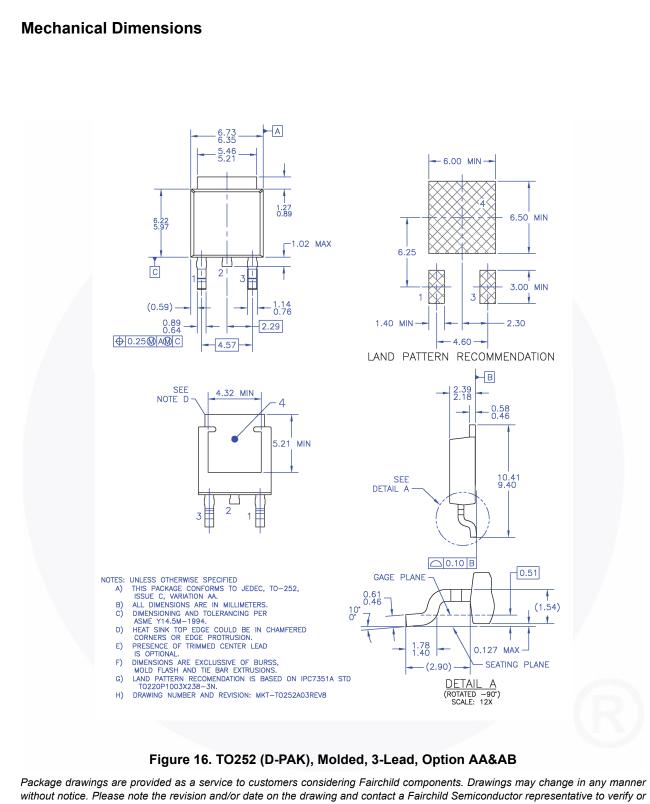
## ©2008 Fairchild Semiconductor Corporation FCD7N60 Rev. C1





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